

Si Photo Diode Chip--ORT212650PD

1. Scope:

- The specification applies to NIP silicon photo-diode chips.
- Type: ORT212650PD

2. Structure:

- NIP planar type.
- Top (Cathode) Side: aluminum(Al) alloy.
- Back (Anode) Side: silver(Ag) alloy.

3. Size: (26mil×50mil)

- Chip size : 660μm × 1270μm ± 30μm
- Chip thickness : 300μm ± 25μm
- Active area : 500μm × 1110μm ±20μm
- Pad size : 130μm ± 10μm
- Pattern drawing: per fig. 1

4. Electro-Optical Characteristics:

(Ta=+25°C)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Forward voltage	V_F	$I_F=10\text{mA}$, $H=0$	0.5		1.3	V
Reverse Breakdown voltage	V_{BR}	$I_R=100\mu\text{A}$, $H=0$	30			V
Reverse Dark Current	I_D	$V_R=10\text{V}$, $H=0$			10	nA
Light Current	I_L	$V_R=5\text{V}$, Has $1\text{mw}/\text{cm}^2$, @ 940nm		22		μA
Peak Sensing wavelength	λ_P			940		nm
Junction Capacitance	C_J	$V_R=3\text{V}$, $F=1\text{MHz}$		12		pF

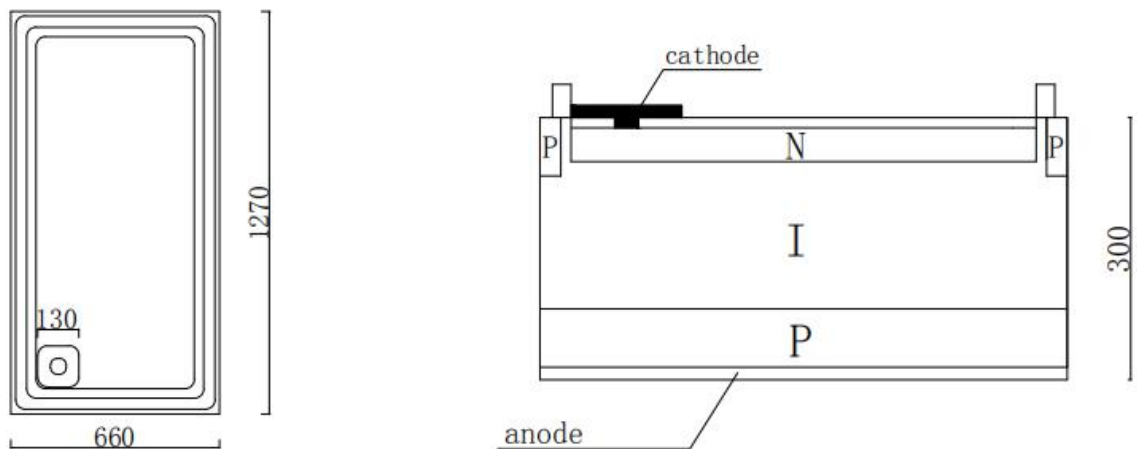


Fig.1



5. Spectral Response

